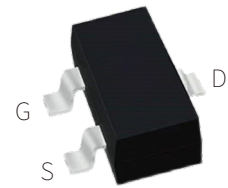


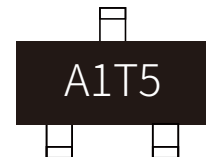
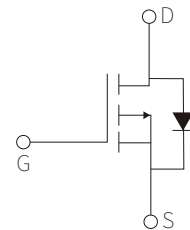
FEATURES

- | High Density Cell Design For Low $R_{DS(on)}$
- | Voltage Controlled Small Signal Switch
- | Rugged and Reliable
- | High Saturation Current Capability
- | Lead free product is acquired


SOT-23

APPLICATION

- | Direct logic-level interface: TTL/CMOS
- | Drivers: relays, solenoids, lamps
- | hammers, display, memories, etc.
- | Battery operated systems
- | Solid-state relays


Marking

Schematic Symbol

APPROVALS

RoHS	Compliance with 2011/65/EU
HF	Compliance with IEC61249-2-21:2003

ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Maximum Drain Current - Continuous	I_D	-3	A
Gate-Source Voltage	V_{GS}	± 12	V
Maximum Power Dissipation	P_D	1	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	125	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	-55 to 150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
Drain-source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-20	-24		V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	uA
Gate-body leakage current	I _{GSS1}	V _{GS} =±12V, V _{DS} =0V			±100	nA
On Characteristics^(Note 3)						
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.7	-1	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-3A		64	110	mΩ
		V _{GS} =-2.5V, I _D =-2A		89	140	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-2A	5			S
Dynamic Characteristics^(Note4)						
Input capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0V, f=1MHz		405		pF
Output capacitance	C _{oss}			75		pF
Reverse transfer capacitance	C _{rss}			55		pF
Switching Characteristics^(Note4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V, I _D =-1A V _{GS} =-4.5V, R _{GEN} =10Ω		11		nS
Turn-on Rise Time	t _r			35		nS
Turn-Off Delay Time	t _{d(off)}			30		nS
Turn-Off Fall Time	t _f			10		nS
Total Gate Charge	Q _g	V _{DS} =-10V, I _D =-3A		3.3	12	nC
Gate-Source Charge	Q _{gs}			0.7		nC
Gate-Drain Charge	Q _{gd}			1.3		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =1.3A			-1.2	V
Diode Forward Current ^(Note 2)	I _S				-3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

PARAMETER CHARACTERISTIC CURVE

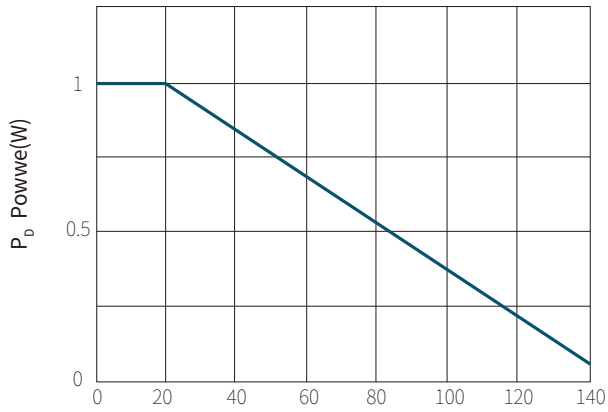
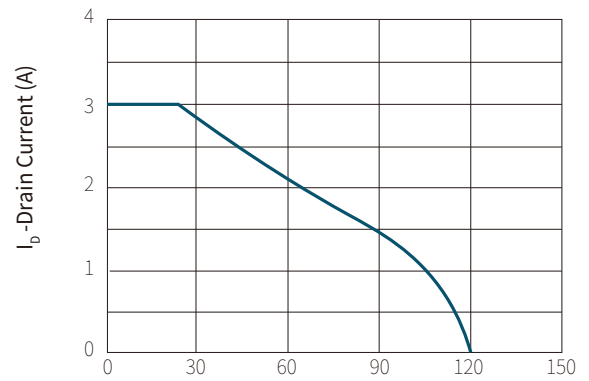
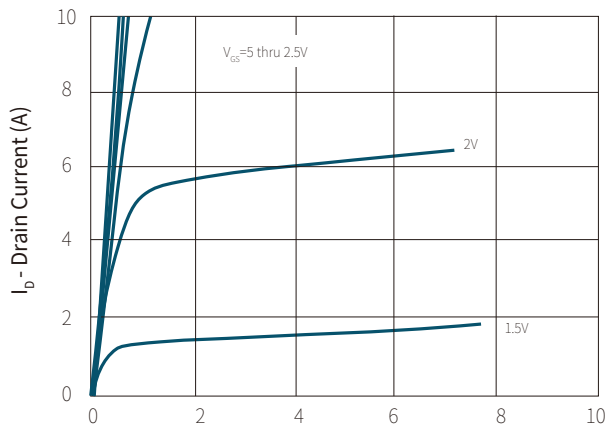
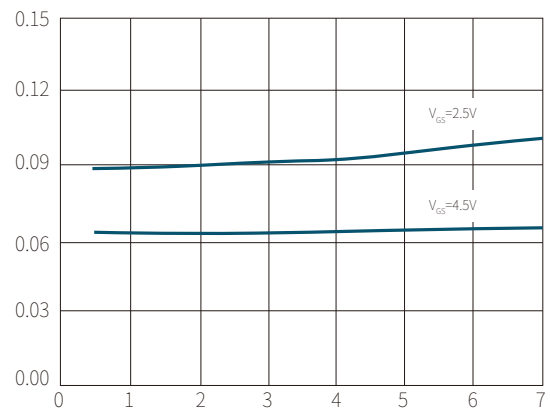
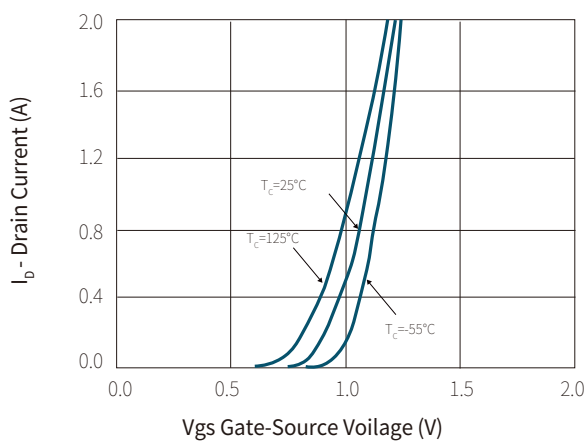
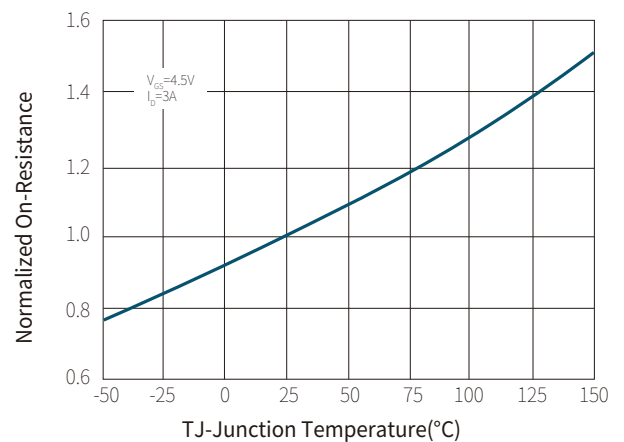
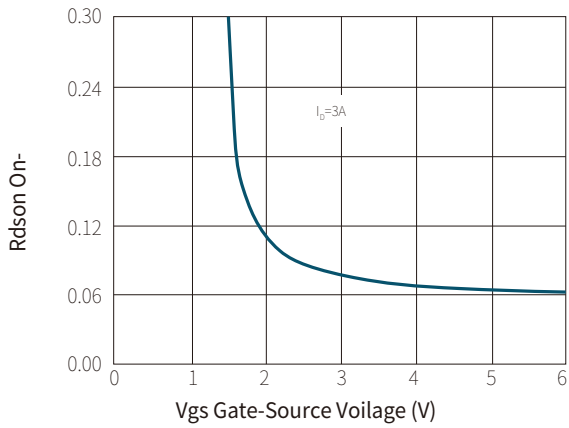
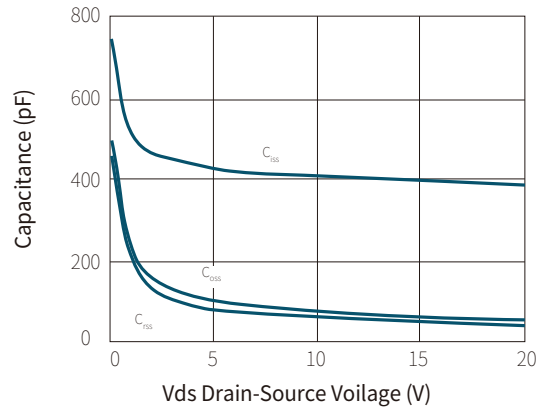
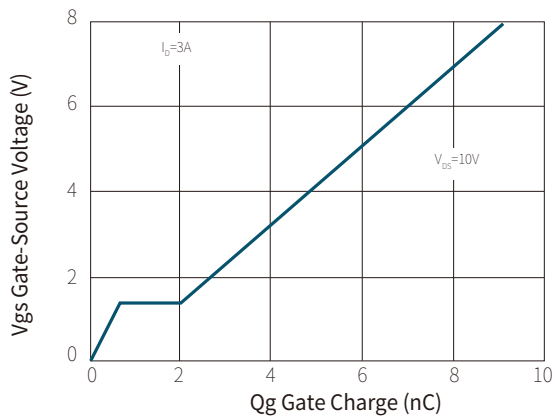
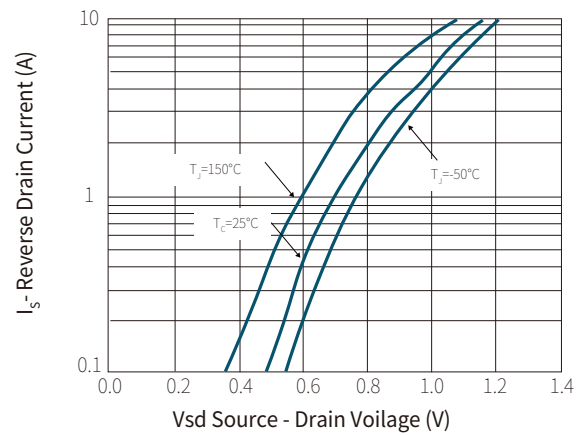
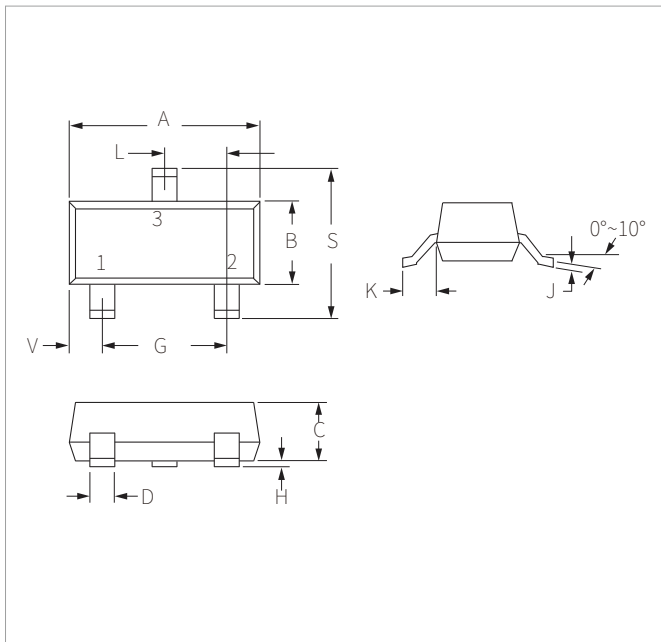
Figure 1: Power Dissipation

Figure 2: Drain Current

Figure 3: Output Characteristics

Figure 4: Drain-Source On-Resistance

Figure 5: Transfer Characteristics

Figure 6: Drain-Source On-Resistance


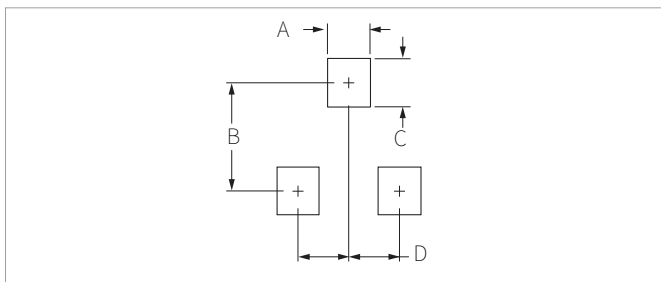
Figure 7: Rdson vs Vgs

Figure 8: Capacitance vs Vds

Figure 9: Gate Charge

Figure 10: Source- Drain Diode Forward


SOT-23 PACKAGE INFORMATION



Ref.	Millimeters		Inches	
	Min	Max	Min	Max
A	2.80	3.04	0.110	0.120
B	1.20	1.40	0.047	0.055
C	0.89	1.11	0.035	0.044
D	0.37	0.50	0.015	0.020
G	1.78	2.04	0.070	0.081
H	0.01	0.100	0.001	0.004
J	0.085	0.180	0.003	0.007
K	0.35	0.69	0.014	0.029
L	0.89	1.02	0.035	0.040
S	2.10	2.64	0.083	0.104
V	0.45	0.60	0.018	0.024

RECOMMENDED PAD LAYOUT DIMENSIONS



Ref.	Millimeters		Inches	
	Min	Max	Min	Max
A	0.71	0.97	0.028	0.038
B	1.88	2.13	0.074	0.084
C	0.71	0.97	0.028	0.038
D	0.81	1.07	0.032	0.042

ORDERING INFORMATION

Part Number	Component Package	QTY/Reel	Reel Size
SI2301	SOT-23	3000PCS	7"

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